

Features

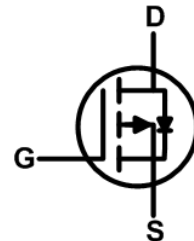
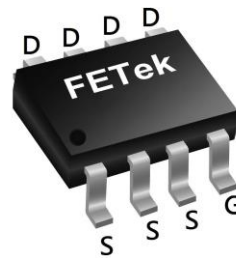
- Advanced Trench MOS Technology
- Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available

Applications

- Load Switch.
- Power Management.
- DC/DC Converter.
- LED Backlighting.

Product Summary


BVDSS	RDSON	ID
-60V	35mΩ	-7.8A

SOP8 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-7.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-6.2	A
I_{DM}	Pulsed Drain Current ²	-32	A
EAS	Single Pulse Avalanche Energy ³	20	mJ
I_{AS}	Avalanche Current	-20	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	3.1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	75	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹ ($t \leq 10S$)	---	40	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-7A$	---	---	35	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	---	---	55	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	---	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-7A$	---	24	---	nC
Q_{gs}	Gate-Source Charge		---	8.6	---	
Q_{gd}	Gate-Drain Charge		---	7.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-7A$	---	9	---	ns
T_r	Rise Time		---	70.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	59.8	---	
T_f	Fall Time		---	20.4	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	2217	---	pF
C_{oss}	Output Capacitance		---	310	---	
C_{rss}	Reverse Transfer Capacitance		---	238	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-7.8	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-7A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	30	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	45	---	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The EAS data shows Max. rating. The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1\text{mH}, I_{AS}=-20A$
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

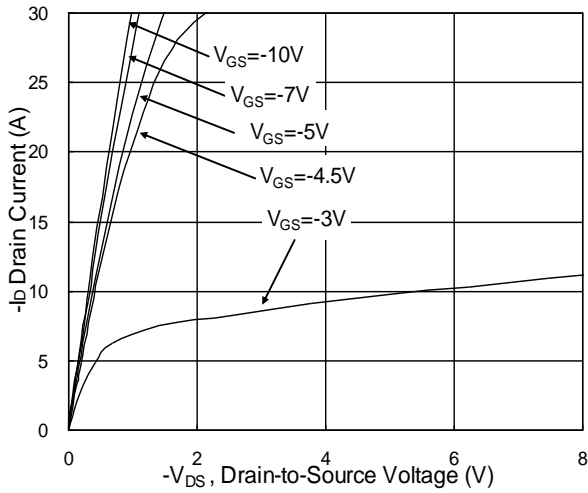


Fig.1 Typical Output Characteristics

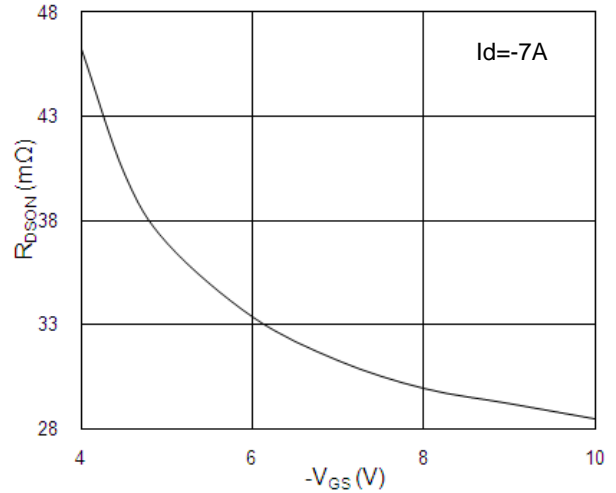


Fig.2 On-Resistance vs G-S Voltage

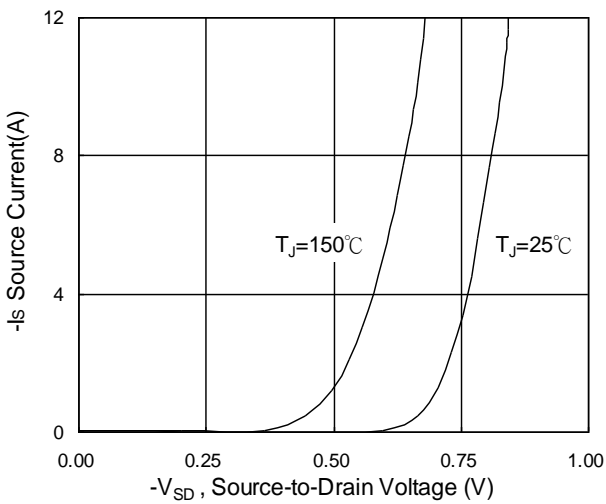


Fig.3 Source Drain Forward Characteristics

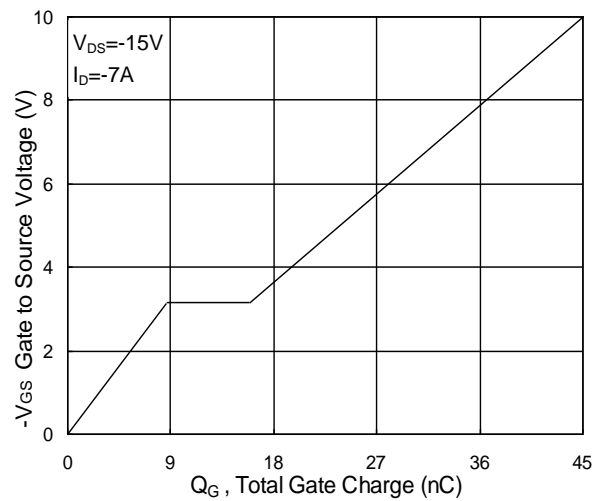


Fig.4 Gate-Charge Characteristics

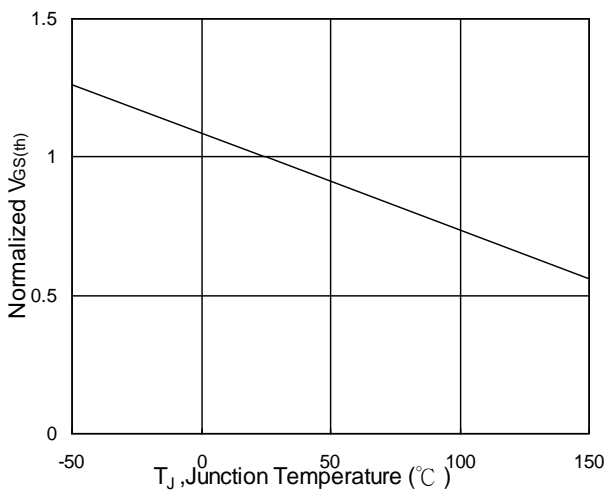


Fig.5 Normalized $V_{GS(th)}$ vs T_J

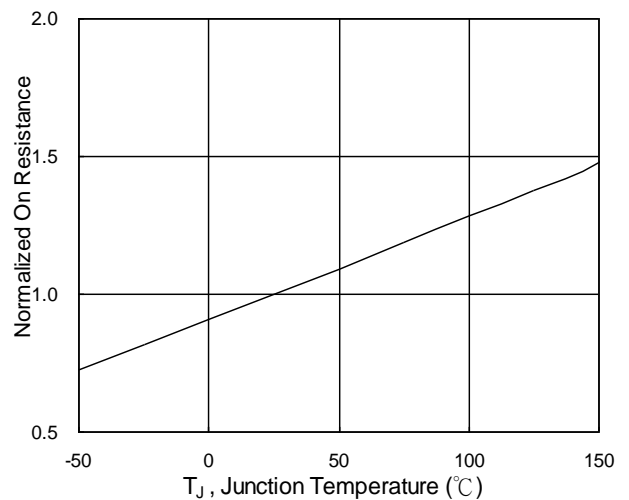


Fig.6 Normalized $R_{DS(on)}$ vs T_J

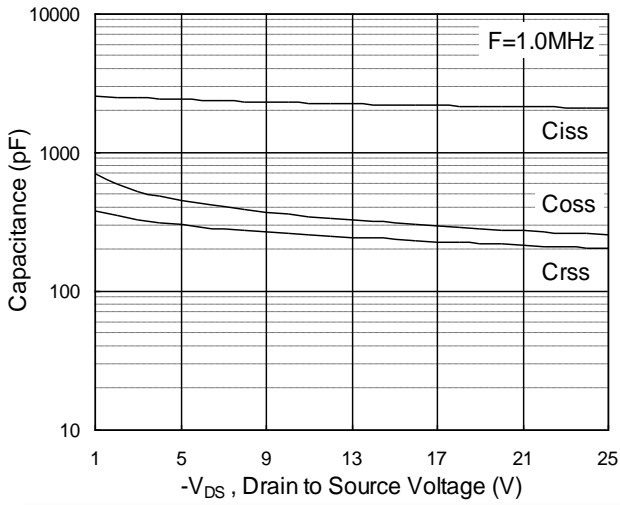


Fig.7 Capacitance

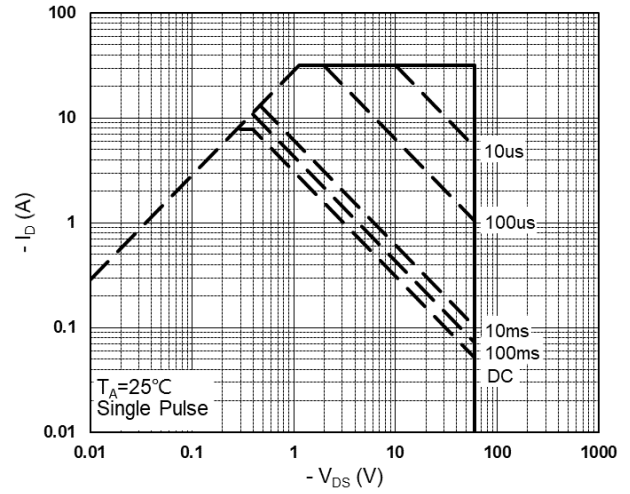


Fig.8 Safe Operating Area

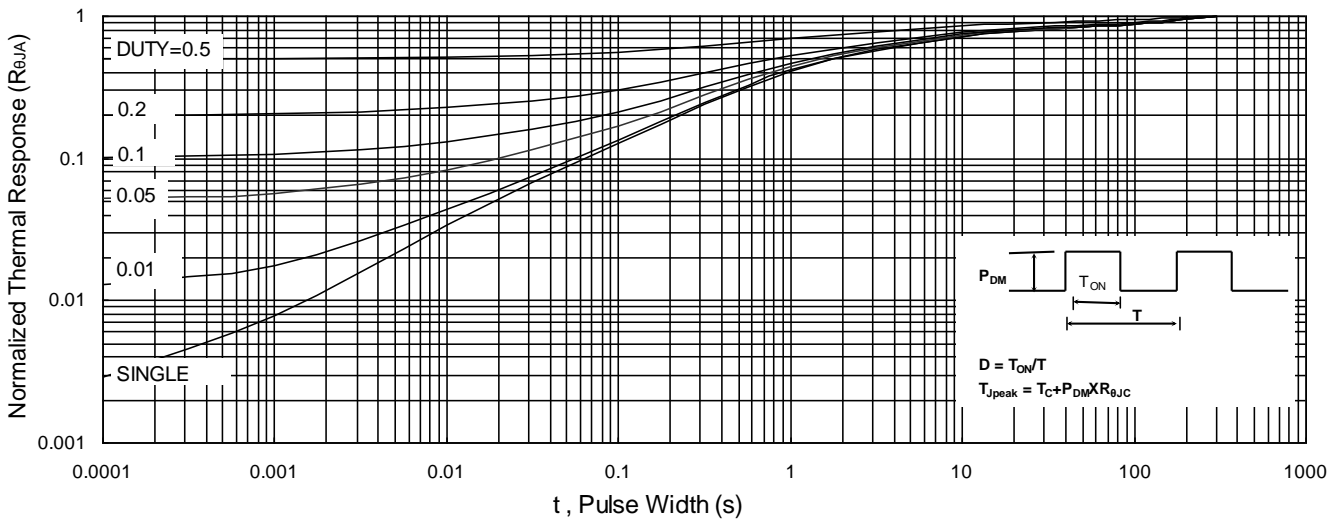


Fig.9 Normalized Maximum Transient Thermal Impedance

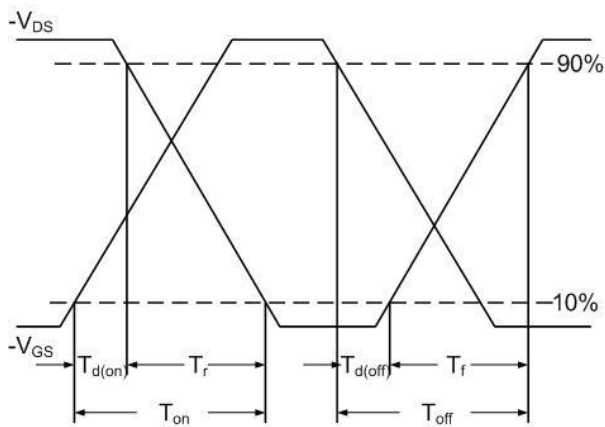


Fig.10 Switching Time Waveform

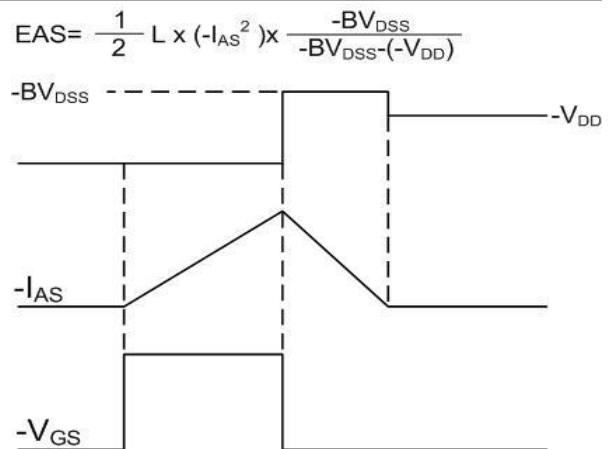


Fig.11 Unclamped Inductive Waveform